IN THE CLAIMS

1. **(original)** A method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region; and

irradiating a second laser beam to the thin-film in such a way as not to overlap with the first irradiated region, thereby forming a second irradiated region and a non-irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the second irradiated region and the non-irradiated region.

2. **(original)** The method according to claim 1, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

3. **(currently amended)** The ~~met~~ method according to claim 1, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

4. **(original)** The method according to claim 1, wherein the first irradiated region serves as an annealed semiconductor region, in which an active region of a TFT is formed.

5. **(original)** The method according to claim 1, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

6. **(original)** The method according to claim 1, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

7. **(original)** The method according to claim 1, wherein an excimer laser is used to generate the first laser beam.

8. **(original)** A method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region; and

irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region or between the second irradiated region and a remaining non-irradiated region of the thin-film.

9. **(original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

10. **(original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

11. (original) The method according to claim 8, wherein the first irradiated region serves as a annealed semiconductor region, in which an active region of a TFT is formed.

12. (original) The method according to claim 8, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

13. (original) The method according to claim 8, wherein the semiconductor thin-film is made of poly-Si film (polysilicon).

14. (original) The method according to claim 8, wherein an excimer laser is used to generate the first laser beam.

15. (currently amended) A [[The]] method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a whole semiconductor thin-film to form a first irradiated region; and

irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region.

16. **(original)** The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

17. **(original)** The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

18. **(original)** The method according to claim 15, wherein the first irradiated region serves as an annealed semiconductor region, in which an active region of a TFT is formed.

19. **(original)** The method according to claim 15, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

20. **(original)** The method according to claim 15, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

21. **(original)** The method according to claim 15, wherein an excimer laser is used to generate the first laser beam.

22. **(currently amended)** A laser apparatus comprising:

a movable stage adapted to position ~~on which~~ a target ~~is place~~;

a first laser beam adapted to generate ~~for generating~~ a first laser beam;

a first optical system, the first laser beam being configured by [[a]] the first optical system to be irradiated to a semiconductor thin-film as the target on the stage;

a second laser beam generator for generating a second laser beam; and

a second optical system, the second laser beam being configured by [[a]] the second optical system to be irradiated to the thin-film in such a way as to be coaxial with the first laser beam when a movable optical element included in the second optical system is positioned in a first position in an optical path of the first laser beam;

wherein the first laser beam and the second laser beam are adapted to irradiate to the thin-film to form an alignment mark using an optical constant difference.

23. (previously presented) The apparatus according to claim 22, wherein the first laser beam generator and the second laser beam generator are different in size from each other.

24. (previously presented) The apparatus according to claim 22, wherein an excimer laser is used as the first laser beam generator.

25. (previously presented) The apparatus according to claim 22, wherein the optical element included in the second optical system is movable between the first position in the optical path of the first laser beam and a second position outside the same optical path.

26. (previously presented) The apparatus according to claim 22, wherein when the first laser beam is irradiated to the target, the element is in the second position;

and wherein when the second laser beam is irradiated to the target, the element is in the first position.